

**AMENDMENTS TO THE CLAIMS**

~~{c19}~~19. (Currently Amended) A method of fabricating a semiconductor chip, comprising the steps of:

- (a) providing a semiconductor substrate comprising a first dopant type at a first dopant level;
  - (b) forming a rectifying diffusion contact in said substrate;
  - (c) forming a non-rectifying diffusion contact in said substrate, said non-rectifying diffusion contact having a second dopant level different than the first dopant level;
- and
- (d) forming a halo diffusion adjacent said rectifying diffusion contact and forming no halo diffusion adjacent said non-rectifying diffusion contact.

~~{c20}~~20. (Currently Amended) A method as recited in claim 19, wherein in said forming step (b) said rectifying diffusion is a source/drain diffusion of an FET, wherein in said forming step (c) said non-rectifying contact is a body contact for said FET.

~~{c21}~~21. (Currently Amended) A method as recited in claim 19, wherein said non-rectifying diffusion contact is an electrode of a lateral diode.

~~{c22}~~22. (Currently Amended) A method as recited in claim 21, wherein said lateral diode is for ESD protection, overshoot/undershoot protection, or over voltage clamping.

~~{c23}~~23. (Currently Amended) A method as recited in claim 21, wherein in said forming step (b) said rectifying diffusion is a source/drain diffusion of an FET or a second electrode of said lateral diode.

~~{c24}~~24.(Currently Amended) A method as recited in claim 19, wherein in said forming step (b) said rectifying diffusion is a source/drain diffusion of an FET, wherein said forming step (c) comprises forming a device having a pair of said non-rectifying diffusion contacts and wherein said step (d) comprises forming no halo diffusion adjacent either of said non-rectifying contacts.

~~{c25}~~25.(Currently Amended) A method as recited in claim 24, wherein said device comprises a resistor or a capacitor.

~~{c26}~~26.(Currently Amended) A method as recited in claim 19, wherein in said forming step (a) said substrate comprises SOI.

~~{c27}~~27.(Currently Amended) A method as recited in claim 19, further comprising forming an extension diffusion adjacent said rectifying contact diffusion and forming no extension diffusion adjacent said non-rectifying contact diffusion .

~~{c28}~~28.(Currently Amended) A method as recited in claim 19, wherein said forming step (d) comprises providing a first mask including a location of a non-rectifying diffusion contact, wherein said first mask has a blocking region over said location.

~~{c29}~~29.(Currently Amended) A method as recited in claim 28, wherein said non-rectifying diffusion contact is defined by data on at least one other mask, and wherein said blocking region on said first mask is generated from said data.

~~{c30}~~30.(Currently Amended) A method as recited in claim 29, wherein said blocking region on said first mask is generated from said data by logically combining shapes from a plurality of masks and adjusting the result to avoid sublithographic features.